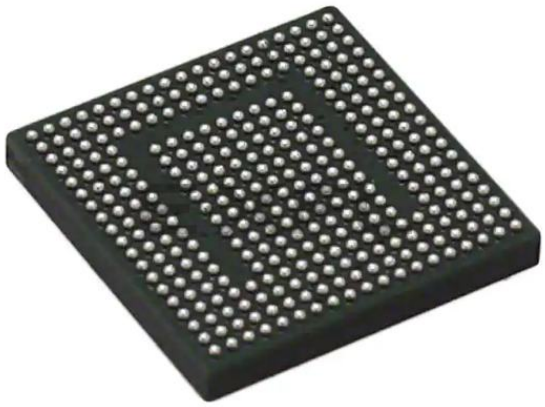
Lattice Semiconductor Corporation - LFE3-17EA-6MG328C Datasheet



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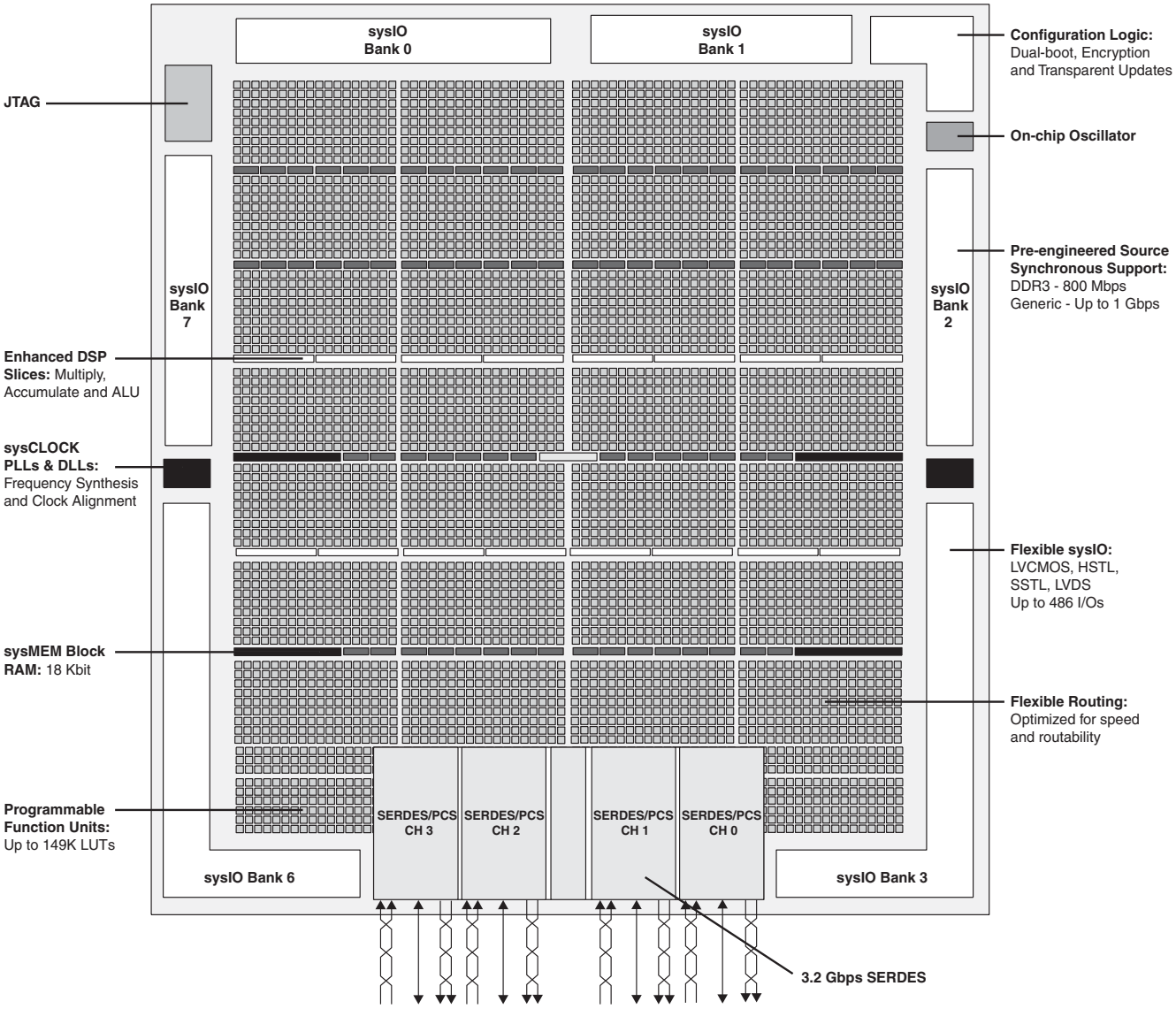
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	2125
Number of Logic Elements/Cells	17000
Total RAM Bits	716800
Number of I/O	116
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	328-LFBGA, CSBGA
Supplier Device Package	328-CSBGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-17ea-6mg328c

Figure 2-1. Simplified Block Diagram, LatticeECP3-35 Device (Top Level)



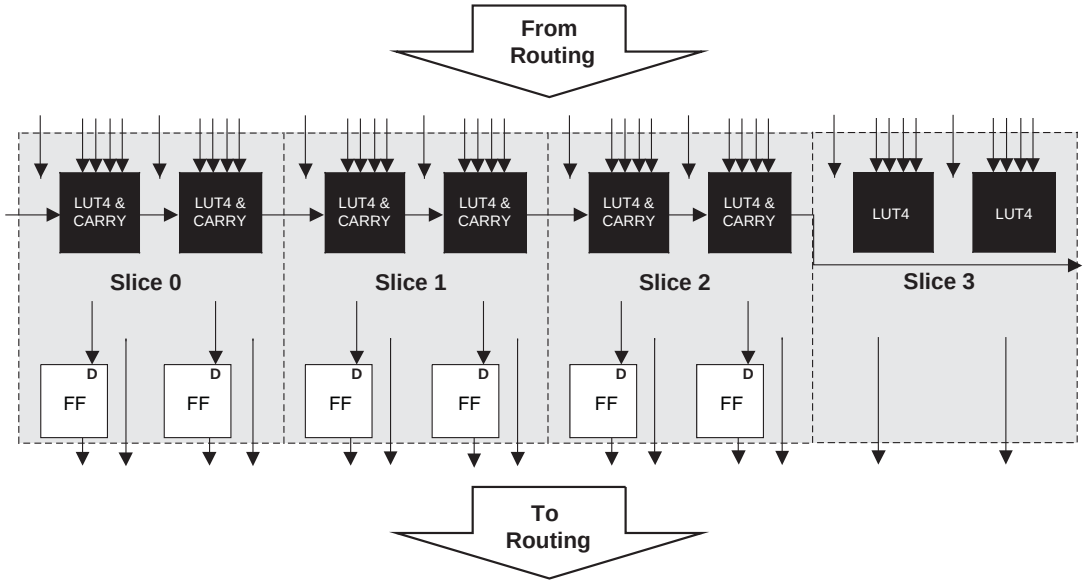
Note: There is no Bank 4 or Bank 5 in LatticeECP3 devices.

PFU Blocks

The core of the LatticeECP3 device consists of PFU blocks, which are provided in two forms, the PFU and PFF. The PFUs can be programmed to perform Logic, Arithmetic, Distributed RAM and Distributed ROM functions. PFF blocks can be programmed to perform Logic, Arithmetic and ROM functions. Except where necessary, the remainder of this data sheet will use the term PFU to refer to both PFU and PFF blocks.

Each PFU block consists of four interconnected slices numbered 0-3 as shown in Figure 2-2. Each slice contains two LUTs. All the interconnections to and from PFU blocks are from routing. There are 50 inputs and 23 outputs associated with each PFU block.

Figure 2-2. PFU Diagram



Slice

Slice 0 through Slice 2 contain two LUT4s feeding two registers, whereas Slice 3 contains two LUT4s only. For PFUs, Slice 0 through Slice 2 can be configured as distributed memory, a capability not available in the PFF. Table 2-1 shows the capability of the slices in both PFF and PFU blocks along with the operation modes they enable. In addition, each PFU contains logic that allows the LUTs to be combined to perform functions such as LUT5, LUT6, LUT7 and LUT8. There is control logic to perform set/reset functions (programmable as synchronous/asynchronous), clock select, chip-select and wider RAM/ROM functions.

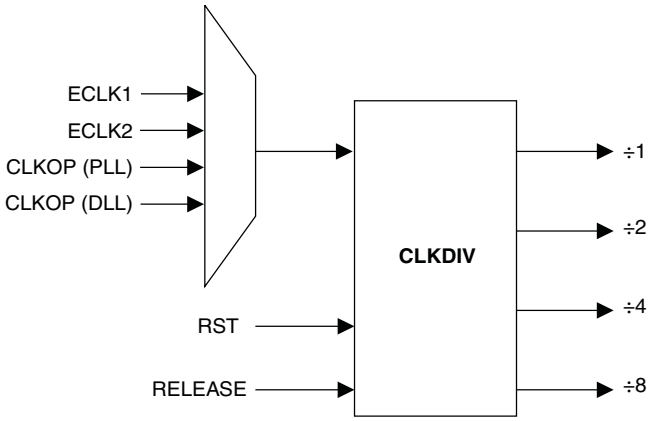
Table 2-1. Resources and Modes Available per Slice

Slice	PFU BLock		PFF Block	
	Resources	Modes	Resources	Modes
Slice 0	2 LUT4s and 2 Registers	Logic, Ripple, RAM, ROM	2 LUT4s and 2 Registers	Logic, Ripple, ROM
Slice 1	2 LUT4s and 2 Registers	Logic, Ripple, RAM, ROM	2 LUT4s and 2 Registers	Logic, Ripple, ROM
Slice 2	2 LUT4s and 2 Registers	Logic, Ripple, RAM, ROM	2 LUT4s and 2 Registers	Logic, Ripple, ROM
Slice 3	2 LUT4s	Logic, ROM	2 LUT4s	Logic, ROM

Figure 2-3 shows an overview of the internal logic of the slice. The registers in the slice can be configured for positive/negative and edge triggered or level sensitive clocks.

Slices 0, 1 and 2 have 14 input signals: 13 signals from routing and one from the carry-chain (from the adjacent slice or PFU). There are seven outputs: six to routing and one to carry-chain (to the adjacent PFU). Slice 3 has 10 input signals from routing and four signals to routing. Table 2-2 lists the signals associated with Slice 0 to Slice 2.

Figure 2-8. Clock Divider Connections



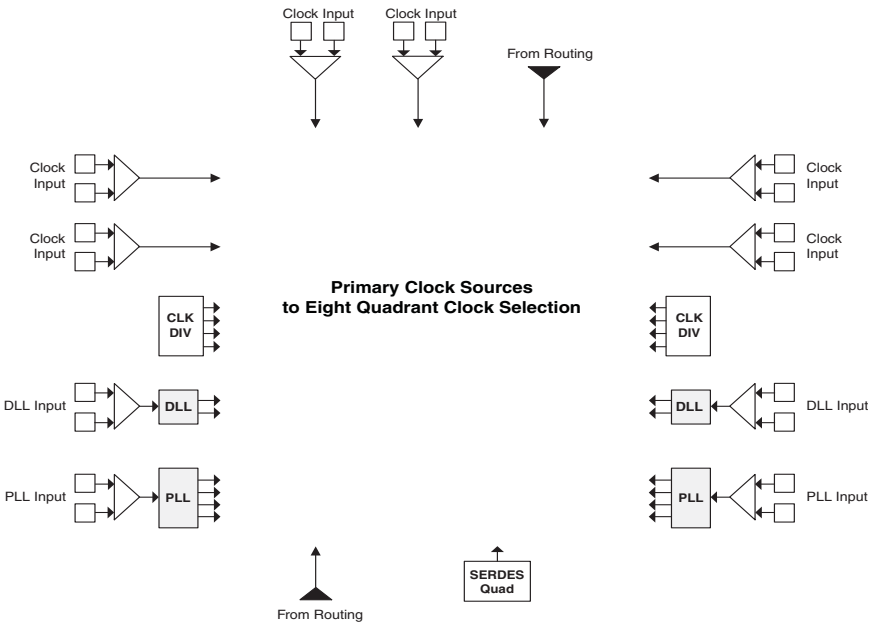
Clock Distribution Network

LatticeECP3 devices have eight quadrant-based primary clocks and eight secondary clock/control sources. Two high performance edge clocks are available on the top, left, and right edges of the device to support high speed interfaces. These clock sources are selected from external I/Os, the sysCLOCK PLLs, DLLs or routing. These clock sources are fed throughout the chip via a clock distribution system.

Primary Clock Sources

LatticeECP3 devices derive clocks from six primary source types: PLL outputs, DLL outputs, CLKDIV outputs, dedicated clock inputs, routing and SERDES Quads. LatticeECP3 devices have two to ten sysCLOCK PLLs and two DLLs, located on the left and right sides of the device. There are six dedicated clock inputs: two on the top side, two on the left side and two on the right side of the device. Figures 2-9, 2-10 and 2-11 show the primary clock sources for LatticeECP3 devices.

Figure 2-9. Primary Clock Sources for LatticeECP3-17

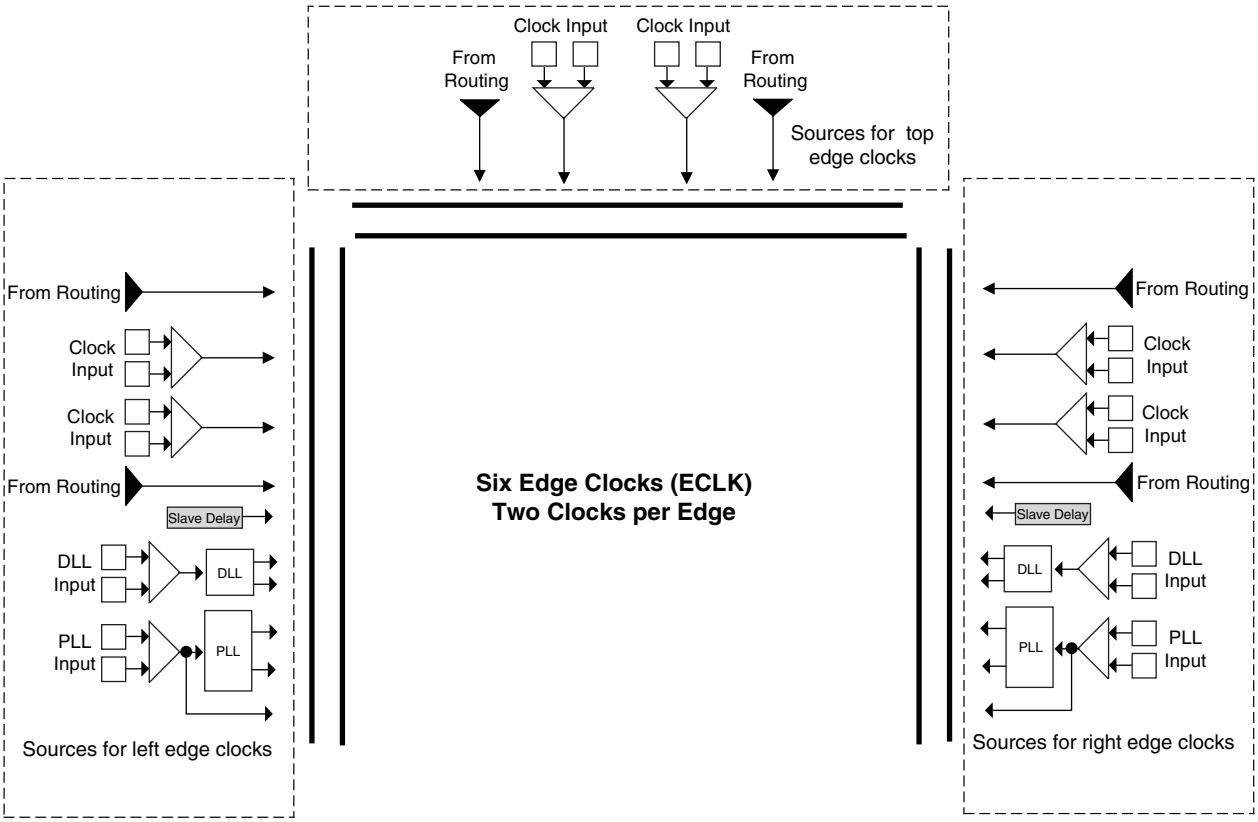


Note: Clock inputs can be configured in differential or single-ended mode.

Edge Clock Sources

Edge clock resources can be driven from a variety of sources at the same edge. Edge clock resources can be driven from adjacent edge clock PIOs, primary clock PIOs, PLLs, DLLs, Slave Delay and clock dividers as shown in Figure 2-19.

Figure 2-19. Edge Clock Sources



Notes:
1. Clock inputs can be configured in differential or single ended mode.
2. The two DLLs can also drive the two top edge clocks.
3. The top left and top right PLL can also drive the two top edge clocks.

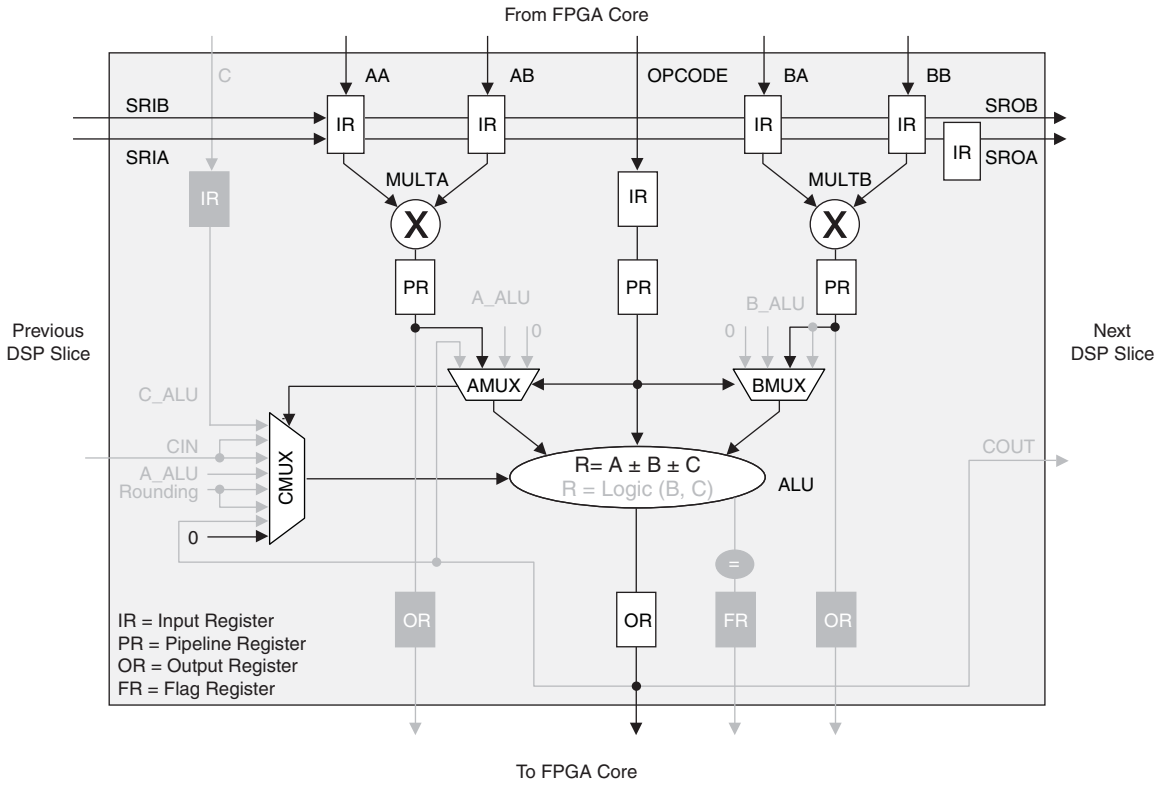
Edge Clock Routing

LatticeECP3 devices have a number of high-speed edge clocks that are intended for use with the PIOs in the implementation of high-speed interfaces. There are six edge clocks per device: two edge clocks on each of the top, left, and right edges. Different PLL and DLL outputs are routed to the two muxes on the left and right sides of the device. In addition, the CLKINDEL signal (generated from the DLL Slave Delay Line block) is routed to all the edge clock muxes on the left and right sides of the device. Figure 2-20 shows the selection muxes for these clocks.

MULTADDSUB DSP Element

In this case, the operands AA and AB are multiplied and the result is added/subtracted with the result of the multiplier operation of operands BA and BB. The user can enable the input, output and pipeline registers. Figure 2-29 shows the MULTADDSUB sysDSP element.

Figure 2-29. MULTADDSUB



Two adjacent PIOs can be joined to provide a differential I/O pair (labeled as “T” and “C”) as shown in Figure 2-32. The PAD Labels “T” and “C” distinguish the two PIOs. Approximately 50% of the PIO pairs on the left and right edges of the device can be configured as true LVDS outputs. All I/O pairs can operate as LVDS inputs.

Table 2-11. PIO Signal List

Name	Type	Description
INDD	Input Data	Register bypassed input. This is not the same port as INCK.
IPA, INA, IPB, INB	Input Data	Ports to core for input data
OPOSA, ONEGA[1], OPOSB, ONEGB[1]	Output Data	Output signals from core. An exception is the ONEGB port, used for tristate logic at the DQS pad.
CE	PIO Control	Clock enables for input and output block flip-flops.
SCLK	PIO Control	System Clock (PCLK) for input and output/TS blocks. Connected from clock ISB.
LSR	PIO Control	Local Set/Reset
ECLK1, ECLK2	PIO Control	Edge clock sources. Entire PIO selects one of two sources using mux.
ECLKDQSR[1]	Read Control	From DQS_STROBE, shifted strobe for memory interfaces only.
DDRCLKPOL[1]	Read Control	Ensures transfer from DQS domain to SCLK domain.
DDRLAT[1]	Read Control	Used to guarantee INDDRX2 gearing by selectively enabling a D-Flip-Flop in datapath.
DEL[3:0]	Read Control	Dynamic input delay control bits.
INCK	To Clock Distribution and PLL	PIO treated as clock PIO, path to distribute to primary clocks and PLL.
TS	Tristate Data	Tristate signal from core (SDR)
DQCLK0[1], DQCLK1[1]	Write Control	Two clocks edges, 90 degrees out of phase, used in output gearing.
DQSW[2]	Write Control	Used for output and tristate logic at DQS only.
DYNDEL[7:0]	Write Control	Shifting of write clocks for specific DQS group, using 6:0 each step is approximately 25ps, 128 steps. Bit 7 is an invert (timing depends on input frequency). There is also a static control for this 8-bit setting, enabled with a memory cell.
DCNTL[6:0]	PIO Control	Original delay code from DDR DLL
DATAVALID[1]	Output Data	Status flag from DATAVALID logic, used to indicate when input data is captured in IOLOGIC and valid to core.
READ	For DQS_Strobe	Read signal for DDR memory interface
DQSI	For DQS_Strobe	Unshifted DQS strobe from input pad
PRMBDET	For DQS_Strobe	DQSI biased to go high when DQSI is tristate, goes to input logic block as well as core logic.
GSRN	Control from routing	Global Set/Reset

1. Signals available on left/right/top edges only.
2. Selected PIO.

PIO

The PIO contains four blocks: an input register block, output register block, tristate register block and a control logic block. These blocks contain registers for operating in a variety of modes along with the necessary clock and selection logic.

Input Register Block

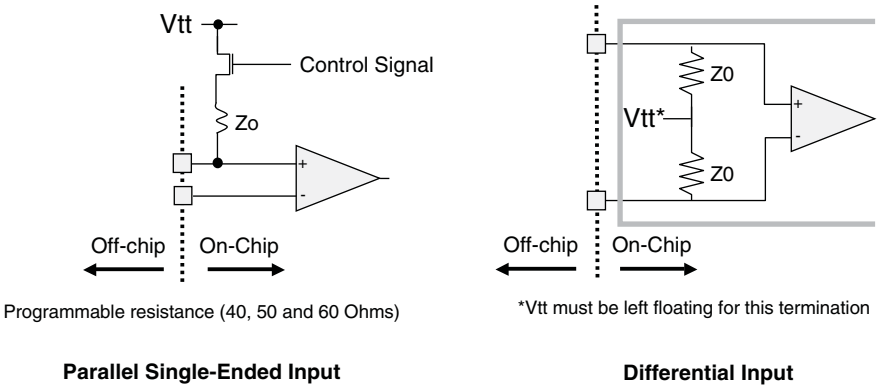
The input register blocks for the PIOs, in the left, right and top edges, contain delay elements and registers that can be used to condition high-speed interface signals, such as DDR memory interfaces and source synchronous interfaces, before they are passed to the device core. Figure 2-33 shows the input register block for the left, right and top edges. The input register block for the bottom edge contains one element to register the input signal and no DDR registers. The following description applies to the input register block for PIOs in the left, right and top edges only.

On-Chip Programmable Termination

The LatticeECP3 supports a variety of programmable on-chip terminations options, including:

- Dynamically switchable Single-Ended Termination with programmable resistor values of 40, 50, or 60 Ohms. External termination to Vtt should be used for DDR2 and DDR3 memory controller implementation.
- Common mode termination of 80, 100, 120 Ohms for differential inputs

Figure 2-39. On-Chip Termination



See Table 2-12 for termination options for input modes.

Table 2-12. On-Chip Termination Options for Input Modes

IO_TYPE	TERMINATE to VTT[1, 2]	DIFFERENTIAL TERMINATION RESISTOR[1]
LVDS25	þ	80, 100, 120
BLVDS25	þ	80, 100, 120
MLVDS	þ	80, 100, 120
HSTL18_I	40, 50, 60	þ
HSTL18_II	40, 50, 60	þ
HSTL18D_I	40, 50, 60	þ
HSTL18D_II	40, 50, 60	þ
HSTL15_I	40, 50, 60	þ
HSTL15D_I	40, 50, 60	þ
SSTL25_I	40, 50, 60	þ
SSTL25_II	40, 50, 60	þ
SSTL25D_I	40, 50, 60	þ
SSTL25D_II	40, 50, 60	þ
SSTL18_I	40, 50, 60	þ
SSTL18_II	40, 50, 60	þ
SSTL18D_I	40, 50, 60	þ
SSTL18D_II	40, 50, 60	þ
SSTL15	40, 50, 60	þ
SSTL15D	40, 50, 60	þ

1. TERMINATE to VTT and DIFFRENTIAL TERMINATION RESISTOR when turned on can only have one setting per bank. Only left and right banks have this feature.
   Use of TERMINATE to VTT and DIFFRENTIAL TERMINATION RESISTOR are mutually exclusive in an I/O bank.
   On-chip termination tolerance +/– 20%
2. External termination to VTT should be used when implementing DDR2 and DDR3 memory controller.

LatticeECP3 Supply Current (Standby)[1, 2, 3, 4, 5, 6]

Over Recommended Operating Conditions

Symbol	Parameter	Device	Typical		Units
			–6L, –7L, –8L	–6, –7, –8	
I_{CC}	Core Power Supply Current	ECP-17EA	29.8	49.4	mA
		ECP3-35EA	53.7	89.4	mA
		ECP3-70EA	137.3	230.7	mA
		ECP3-95EA	137.3	230.7	mA
		ECP3-150EA	219.5	370.9	mA
I_{CCAUX}	Auxiliary Power Supply Current	ECP-17EA	18.3	19.4	mA
		ECP3-35EA	19.6	23.1	mA
		ECP3-70EA	26.5	32.4	mA
		ECP3-95EA	26.5	32.4	mA
		ECP3-150EA	37.0	45.7	mA
I_{CCPLL}	PLL Power Supply Current (Per PLL)	ECP-17EA	0.0	0.0	mA
		ECP3-35EA	0.1	0.1	mA
		ECP3-70EA	0.1	0.1	mA
		ECP3-95EA	0.1	0.1	mA
		ECP3-150EA	0.1	0.1	mA
I_{CCIO}	Bank Power Supply Current (Per Bank)	ECP-17EA	1.3	1.4	mA
		ECP3-35EA	1.3	1.4	mA
		ECP3-70EA	1.4	1.5	mA
		ECP3-95EA	1.4	1.5	mA
		ECP3-150EA	1.4	1.5	mA
I_{CCJ}	JTAG Power Supply Current	All Devices	2.5	2.5	mA
I_{CCA}	Transmit, Receive, PLL and Reference Clock Buffer Power Supply	ECP-17EA	6.1	6.1	mA
		ECP3-35EA	6.1	6.1	mA
		ECP3-70EA	18.3	18.3	mA
		ECP3-95EA	18.3	18.3	mA
		ECP3-150EA	24.4	24.4	mA

1. For further information on supply current, please see the list of technical documentation at the end of this data sheet.
2. Assumes all outputs are tristated, all inputs are configured as LVCMOS and held at the V_{CCIO} or GND.
3. Frequency 0 MHz.
4. Pattern represents a “blank” configuration data file.
5. T_J = 85 °C, power supplies at nominal voltage.
6. To determine the LatticeECP3 peak start-up current data, use the Power Calculator tool.

LatticeECP3 External Switching Characteristics (Continued)[1, 2, 3, 13]

Over Recommended Commercial Operating Conditions

Parameter	Description	Device	–8		–7		–6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Generic DDRX2 Inputs with Clock and Data (>10bits wide) are Aligned at Pin (GDDRX2_RX.ECLK.Aligned) (No CLKDIV)									
Left and Right Sides Using DLLCLKPIN for Clock Input									
$t_{DVACLKGDDR}$	Data Setup Before CLK	ECP3-150EA	—	0.225	—	0.225	—	0.225	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-150EA	0.775	—	0.775	—	0.775	—	UI
f_{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-150EA	—	460	—	385	—	345	MHz
$t_{DVACLKGDDR}$	Data Setup Before CLK	ECP3-70EA/95EA	—	0.225	—	0.225	—	0.225	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-70EA/95EA	0.775	—	0.775	—	0.775	—	UI
f_{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-70EA/95EA	—	460	—	385	—	311	MHz
$t_{DVACLKGDDR}$	Data Setup Before CLK	ECP3-35EA	—	0.210	—	0.210	—	0.210	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-35EA	0.790	—	0.790	—	0.790	—	UI
f_{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-35EA	—	460	—	385	—	311	MHz
$t_{DVACLKGDDR}$	Data Setup Before CLK (Left and Right Sides)	ECP3-17EA	—	0.210	—	0.210	—	0.210	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-17EA	0.790	—	0.790	—	0.790	—	UI
f_{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-17EA	—	460	—	385	—	311	MHz
Top Side Using PCLK Pin for Clock Input									
$t_{DVACLKGDDR}$	Data Setup Before CLK	ECP3-150EA	—	0.225	—	0.225	—	0.225	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-150EA	0.775	—	0.775	—	0.775	—	UI
f_{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-150EA	—	235	—	170	—	130	MHz
$t_{DVACLKGDDR}$	Data Setup Before CLK	ECP3-70EA/95EA	—	0.225	—	0.225	—	0.225	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-70EA/95EA	0.775	—	0.775	—	0.775	—	UI
f_{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-70EA/95EA	—	235	—	170	—	130	MHz
$t_{DVACLKGDDR}$	Data Setup Before CLK	ECP3-35EA	—	0.210	—	0.210	—	0.210	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-35EA	0.790	—	0.790	—	0.790	—	UI
f_{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-35EA	—	235	—	170	—	130	MHz
$t_{DVACLKGDDR}$	Data Setup Before CLK	ECP3-17EA	—	0.210	—	0.210	—	0.210	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	ECP3-17EA	0.790	—	0.790	—	0.790	—	UI
f_{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-17EA	—	235	—	170	—	130	MHz
Generic DDRX2 Inputs with Clock and Data (<10 Bits Wide) Centered at Pin (GDDRX2_RX.DQS.Centered) Using DQS Pin for Clock Input									
Left and Right Sides									
t_{SUGDDR}	Data Setup Before CLK	All ECP3EA Devices	330	—	330	—	352	—	ps
t_{HOGDDR}	Data Hold After CLK	All ECP3EA Devices	330	—	330	—	352	—	ps
f_{MAX_GDDR}	DDRX2 Clock Frequency	All ECP3EA Devices	—	400	—	400	—	375	MHz
Generic DDRX2 Inputs with Clock and Data (<10 Bits Wide) Aligned at Pin (GDDRX2_RX.DQS.Aligned) Using DQS Pin for Clock Input									
Left and Right Sides									
$t_{DVACLKGDDR}$	Data Setup Before CLK	All ECP3EA Devices	—	0.225	—	0.225	—	0.225	UI
$t_{DVECLKGDDR}$	Data Hold After CLK	All ECP3EA Devices	0.775	—	0.775	—	0.775	—	UI
f_{MAX_GDDR}	DDRX2 Clock Frequency	All ECP3EA Devices	—	400	—	400	—	375	MHz
Generic DDRX1 Output with Clock and Data (>10 Bits Wide) Centered at Pin (GDDRX1_TX.SCLK.Centered)[10]									
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-150EA	670	—	670	—	670	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-150EA	670	—	670	—	670	—	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-150EA	—	250	—	250	—	250	MHz
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-70EA/95EA	666	—	665	—	664	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-70EA/95EA	666	—	665	—	664	—	ps

LatticeECP3 External Switching Characteristics (Continued)[1, 2, 3, 13]

Over Recommended Commercial Operating Conditions

Parameter	Description	Device	–8		–7		–6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Generic DDRX2 Output with Clock and Data (>10 Bits Wide) Centered at Pin Using PLL (GDDRX2_TX.PLL.Centered)[10]									
Left and Right Sides									
$t_{DVBGDDR}$	Data Valid Before CLK	All ECP3EA Devices	285	—	370	—	431	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	All ECP3EA Devices	285	—	370	—	432	—	ps
f_{MAX_GDDR}	DDRX2 Clock Frequency	All ECP3EA Devices	—	500	—	420	—	375	MHz
Memory Interface									
DDR/DDR2 I/O Pin Parameters (Input Data are Strobe Edge Aligned, Output Strobe Edge is Data Centered)[4]									
t_{DVADQ}	Data Valid After DQS (DDR Read)	All ECP3 Devices	—	0.225	—	0.225	—	0.225	UI
t_{DVEDQ}	Data Hold After DQS (DDR Read)	All ECP3 Devices	0.64	—	0.64	—	0.64	—	UI
t_{DQVBS}	Data Valid Before DQS	All ECP3 Devices	0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Data Valid After DQS	All ECP3 Devices	0.25	—	0.25	—	0.25	—	UI
f_{MAX_DDR}	DDR Clock Frequency	All ECP3 Devices	95	200	95	200	95	166	MHz
f_{MAX_DDR2}	DDR2 clock frequency	All ECP3 Devices	125	266	125	200	125	166	MHz
DDR3 (Using PLL for SCLK) I/O Pin Parameters									
t_{DVADQ}	Data Valid After DQS (DDR Read)	All ECP3 Devices	—	0.225	—	0.225	—	0.225	UI
t_{DVEDQ}	Data Hold After DQS (DDR Read)	All ECP3 Devices	0.64	—	0.64	—	0.64	—	UI
t_{DQVBS}	Data Valid Before DQS	All ECP3 Devices	0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Data Valid After DQS	All ECP3 Devices	0.25	—	0.25	—	0.25	—	UI
f_{MAX_DDR3}	DDR3 clock frequency	All ECP3 Devices	300	400	266	333	266	300	MHz
DDR3 Clock Timing									
t_{CH} (avg)[9]	Average High Pulse Width	All ECP3 Devices	0.47	0.53	0.47	0.53	0.47	0.53	UI
t_{CL} (avg)[9]	Average Low Pulse Width	All ECP3 Devices	0.47	0.53	0.47	0.53	0.47	0.53	UI
t_{JIT} (per, lck)[9]	Output Clock Period Jitter During DLL Locking Period	All ECP3 Devices	–90	90	–90	90	–90	90	ps
t_{JIT} (cc, lck)[9]	Output Cycle-to-Cycle Period Jitter During DLL Locking Period	All ECP3 Devices	—	180	—	180	—	180	ps

1. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from the Diamond or ispLEVER software.
2. General I/O timing numbers based on LVCMOS 2.5, 12mA, Fast Slew Rate, 0pf load.
3. Generic DDR timing numbers based on LVDS I/O.
4. DDR timing numbers based on SSTL25. DDR2 timing numbers based on SSTL18.
5. DDR3 timing numbers based on SSTL15.
6. Uses LVDS I/O standard.
7. The current version of software does not support per bank skew numbers; this will be supported in a future release.
8. Maximum clock frequencies are tested under best case conditions. System performance may vary upon the user environment.
9. Using settings generated by IPexpress.
10. These numbers are generated using best case PLL located in the center of the device.
11. Uses SSTL25 Class II Differential I/O Standard.
12. All numbers are generated with ispLEVER 8.1 software.
13. For details on -9 speed grade devices, please contact your Lattice Sales Representative.

LatticeECP3 Family Timing Adders[1, 2, 3, 4, 5, 7] (Continued)

Over Recommended Commercial Operating Conditions

Buffer Type	Description	–8	–7	–6	Units
RSDS25	RSDS, VCCIO = 2.5 V	–0.07	–0.04	–0.01	ns
PPLVDS	Point-to-Point LVDS, True LVDS, VCCIO = 2.5 V or 3.3 V	–0.22	–0.19	–0.16	ns
LVPECL33	LVPECL, Emulated, VCCIO = 3.3 V	0.67	0.76	0.86	ns
HSTL18_I	HSTL_18 class I 8mA drive, VCCIO = 1.8 V	1.20	1.34	1.47	ns
HSTL18_II	HSTL_18 class II, VCCIO = 1.8 V	0.89	1.00	1.11	ns
HSTL18D_I	Differential HSTL 18 class I 8 mA drive	1.20	1.34	1.47	ns
HSTL18D_II	Differential HSTL 18 class II	0.89	1.00	1.11	ns
HSTL15_I	HSTL_15 class I 4 mA drive, VCCIO = 1.5 V	1.67	1.83	1.99	ns
HSTL15D_I	Differential HSTL 15 class I 4 mA drive	1.67	1.83	1.99	ns
SSTL33_I	SSTL_3 class I, VCCIO = 3.3 V	1.12	1.17	1.21	ns
SSTL33_II	SSTL_3 class II, VCCIO = 3.3 V	1.08	1.12	1.15	ns
SSTL33D_I	Differential SSTL_3 class I	1.12	1.17	1.21	ns
SSTL33D_II	Differential SSTL_3 class II	1.08	1.12	1.15	ns
SSTL25_I	SSTL_2 class I 8 mA drive, VCCIO = 2.5 V	1.06	1.19	1.31	ns
SSTL25_II	SSTL_2 class II 16 mA drive, VCCIO = 2.5 V	1.04	1.17	1.31	ns
SSTL25D_I	Differential SSTL_2 class I 8 mA drive	1.06	1.19	1.31	ns
SSTL25D_II	Differential SSTL_2 class II 16 mA drive	1.04	1.17	1.31	ns
SSTL18_I	SSTL_1.8 class I, VCCIO = 1.8 V	0.70	0.84	0.97	ns
SSTL18_II	SSTL_1.8 class II 8 mA drive, VCCIO = 1.8 V	0.70	0.84	0.97	ns
SSTL18D_I	Differential SSTL_1.8 class I	0.70	0.84	0.97	ns
SSTL18D_II	Differential SSTL_1.8 class II 8 mA drive	0.70	0.84	0.97	ns
SSTL15	SSTL_1.5, VCCIO = 1.5 V	1.22	1.35	1.48	ns
SSTL15D	Differential SSTL_15	1.22	1.35	1.48	ns
LVTTL33_4mA	LVTTL 4 mA drive, VCCIO = 3.3V	0.25	0.24	0.23	ns
LVTTL33_8mA	LVTTL 8 mA drive, VCCIO = 3.3V	–0.06	–0.06	–0.07	ns
LVTTL33_12mA	LVTTL 12 mA drive, VCCIO = 3.3V	–0.01	–0.02	–0.02	ns
LVTTL33_16mA	LVTTL 16 mA drive, VCCIO = 3.3V	–0.07	–0.07	–0.08	ns
LVTTL33_20mA	LVTTL 20 mA drive, VCCIO = 3.3V	–0.12	–0.13	–0.14	ns
LVCMOS33_4mA	LVCMOS 3.3 4 mA drive, fast slew rate	0.25	0.24	0.23	ns
LVCMOS33_8mA	LVCMOS 3.3 8 mA drive, fast slew rate	–0.06	–0.06	–0.07	ns
LVCMOS33_12mA	LVCMOS 3.3 12 mA drive, fast slew rate	–0.01	–0.02	–0.02	ns
LVCMOS33_16mA	LVCMOS 3.3 16 mA drive, fast slew rate	–0.07	–0.07	–0.08	ns
LVCMOS33_20mA	LVCMOS 3.3 20 mA drive, fast slew rate	–0.12	–0.13	–0.14	ns
LVCMOS25_4mA	LVCMOS 2.5 4 mA drive, fast slew rate	0.12	0.10	0.09	ns
LVCMOS25_8mA	LVCMOS 2.5 8 mA drive, fast slew rate	–0.05	–0.06	–0.07	ns
LVCMOS25_12mA	LVCMOS 2.5 12 mA drive, fast slew rate	0.00	0.00	0.00	ns
LVCMOS25_16mA	LVCMOS 2.5 16 mA drive, fast slew rate	–0.12	–0.13	–0.14	ns
LVCMOS25_20mA	LVCMOS 2.5 20 mA drive, fast slew rate	–0.12	–0.13	–0.14	ns
LVCMOS18_4mA	LVCMOS 1.8 4 mA drive, fast slew rate	0.11	0.12	0.14	ns
LVCMOS18_8mA	LVCMOS 1.8 8 mA drive, fast slew rate	0.11	0.12	0.14	ns
LVCMOS18_12mA	LVCMOS 1.8 12 mA drive, fast slew rate	–0.04	–0.03	–0.03	ns
LVCMOS18_16mA	LVCMOS 1.8 16 mA drive, fast slew rate	–0.04	–0.03	–0.03	ns

sysCLOCK PLL Timing

Over Recommended Operating Conditions

Parameter	Descriptions	Conditions	Clock	Min.	Typ.	Max.	Units
f_{IN}	Input clock frequency (CLKI, CLKFB)		Edge clock	2	—	500	MHz
			Primary clock[4]	2	—	420	MHz
f_{OUT}	Output clock frequency (CLKOP, CLKOS)		Edge clock	4	—	500	MHz
			Primary clock[4]	4	—	420	MHz
f_{OUT1}	K-Divider output frequency	CLKOK		0.03125	—	250	MHz
f_{OUT2}	K2-Divider output frequency	CLKOK2		0.667	—	166	MHz
f_{VCO}	PLL VCO frequency			500	—	1000	MHz
f_{PFD}[3]	Phase detector input frequency		Edge clock	2	—	500	MHz
			Primary clock[4]	2	—	420	MHz
AC Characteristics							
t_{PA}	Programmable delay unit			65	130	260	ps
t_{DT}	Output clock duty cycle (CLKOS, at 50% setting)		Edge clock	45	50	55	%
		$f_{OUT} \leq 250$ MHz	Primary clock	45	50	55	%
		$f_{OUT} > 250$ MHz	Primary clock	30	50	70	%
t_{CPA}	Coarse phase shift error (CLKOS, at all settings)			-5	0	+5	% of period
t_{OPW}	Output clock pulse width high or low (CLKOS)			1.8	—	—	ns
t_{OPJIT}[1]	Output clock period jitter	$f_{OUT} \geq 420$ MHz		—	—	200	ps
		420 MHz > $f_{OUT} \geq 100$ MHz		—	—	250	ps
		$f_{OUT} < 100$ MHz		—	—	0.025	UIPP
t_{SK}	Input clock to output clock skew when N/M = integer			—	—	500	ps
t_{LOCK}[2]	Lock time	2 to 25 MHz		—	—	200	us
		25 to 500 MHz		—	—	50	us
t_{UNLOCK}	Reset to PLL unlock time to ensure fast reset			—	—	50	ns
t_{HI}	Input clock high time	90% to 90%		0.5	—	—	ns
t_{LO}	Input clock low time	10% to 10%		0.5	—	—	ns
t_{IPJIT}	Input clock period jitter			—	—	400	ps
t_{RST}	Reset signal pulse width high, RSTK			10	—	—	ns
	Reset signal pulse width high, RST			500	—	—	ns

1. Jitter sample is taken over 10,000 samples of the primary PLL output with clean reference clock with no additional I/O toggling.
2. Output clock is valid after t_{LOCK} for PLL reset and dynamic delay adjustment.
3. Period jitter and cycle-to-cycle jitter numbers are guaranteed for $f_{PFD} > 4$ MHz. For $f_{PFD} < 4$ MHz, the jitter numbers may not be met in certain conditions. Please contact the factory for $f_{PFD} < 4$ MHz.
4. When using internal feedback, maximum can be up to 500 MHz.

SERDES External Reference Clock

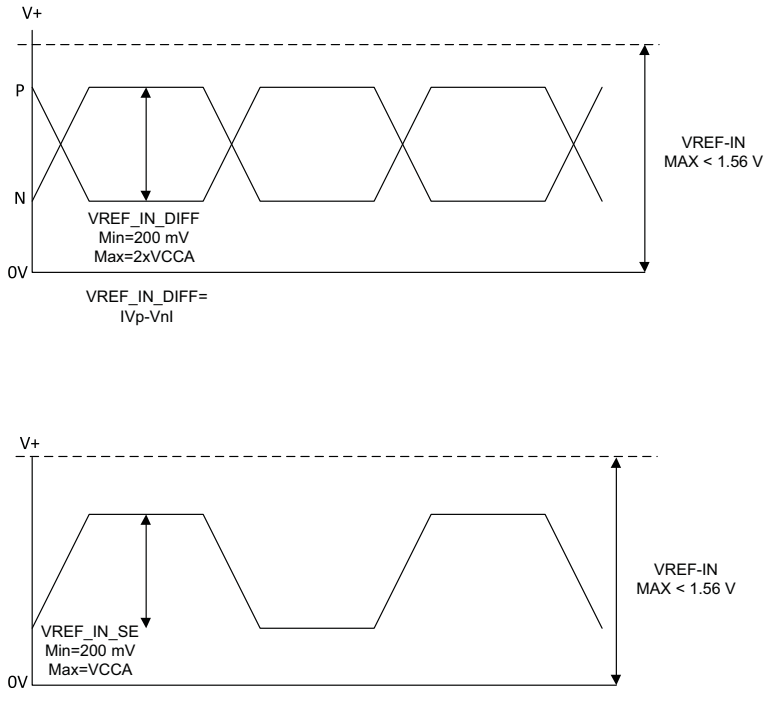
The external reference clock selection and its interface are a critical part of system applications for this product. Table 3-12 specifies reference clock requirements, over the full range of operating conditions.

Table 3-12. External Reference Clock Specification (refclkp/refclkn)

Symbol	Description	Min.	Typ.	Max.	Units
F_{REF}	Frequency range	15	—	320	MHz
$F_{REF-PPM}$	Frequency tolerance[1]	–1000	—	1000	ppm
$V_{REF-IN-SE}$	Input swing, single-ended clock[2]	200	—	V_{CCA}	mV, p-p
$V_{REF-IN-DIFF}$	Input swing, differential clock	200	—	$2*V_{CCA}$	mV, p-p differential
V_{REF-IN}	Input levels	0	—	V_{CCA} + 0.3	V
D_{REF}	Duty cycle[3]	40	—	60	%
T_{REF-R}	Rise time (20% to 80%)	200	500	1000	ps
T_{REF-F}	Fall time (80% to 20%)	200	500	1000	ps
$Z_{REF-IN-TERM-DIFF}$	Differential input termination	–20%	100/2K	+20%	Ohms
$C_{REF-IN-CAP}$	Input capacitance	—	—	7	pF

1. Depending on the application, the PLL_LOL_SET and CDR_LOL_SET control registers may be adjusted for other tolerance values as described in TN1176, LatticeECP3 SERDES/PCS Usage Guide.
2. The signal swing for a single-ended input clock must be as large as the p-p differential swing of a differential input clock to get the same gain at the input receiver. Lower swings for the clock may be possible, but will tend to increase jitter.
3. Measured at 50% amplitude.

Figure 3-13. SERDES External Reference Clock Waveforms



XAUI/Serial Rapid I/O Type 3/CPRI LV E.30 Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-13. Transmit

Over Recommended Operating Conditions

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
T_{RF}	Differential rise/fall time	20%-80%	—	80	—	ps
$Z_{TX\_DIFF\_DC}$	Differential impedance		80	100	120	Ohms
J_{TX_DDJ}[2, 3, 4]	Output data deterministic jitter		—	—	0.17	UI
J_{TX_TJ}[1, 2, 3, 4]	Total output data jitter		—	—	0.35	UI

1. Total jitter includes both deterministic jitter and random jitter.
2. Jitter values are measured with each CML output AC coupled into a 50-Ohm impedance (100-Ohm differential impedance).
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Values are measured at 2.5 Gbps.

Table 3-14. Receive and Jitter Tolerance

Over Recommended Operating Conditions

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
RL_{RX_DIFF}	Differential return loss	From 100 MHz to 3.125 GHz	10	—	—	dB
RL_{RX_CM}	Common mode return loss	From 100 MHz to 3.125 GHz	6	—	—	dB
Z_{RX_DIFF}	Differential termination resistance		80	100	120	Ohms
J_{RX_DJ}[1, 2, 3]	Deterministic jitter tolerance (peak-to-peak)		—	—	0.37	UI
J_{RX_RJ}[1, 2, 3]	Random jitter tolerance (peak-to-peak)		—	—	0.18	UI
J_{RX_SJ}[1, 2, 3]	Sinusoidal jitter tolerance (peak-to-peak)		—	—	0.10	UI
J_{RX_TJ}[1, 2, 3]	Total jitter tolerance (peak-to-peak)		—	—	0.65	UI
T_{RX_EYE}	Receiver eye opening		0.35	—	—	UI

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter. The sinusoidal jitter tolerance mask is shown in Figure 3-18.
2. Jitter values are measured with each high-speed input AC coupled into a 50-Ohm impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Jitter tolerance parameters are characterized when Full Rx Equalization is enabled.
5. Values are measured at 2.5 Gbps.

SMPTE SD/HD-SDI/3G-SDI (Serial Digital Interface) Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-19. Transmit

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
BR_{SDO}	Serial data rate		270	—	2975	Mbps
$T_{JALIGNMENT}$ [2]	Serial output jitter, alignment	270 Mbps	—	—	0.20	UI
$T_{JALIGNMENT}$ [2]	Serial output jitter, alignment	1485 Mbps	—	—	0.20	UI
$T_{JALIGNMENT}$ [1, 2]	Serial output jitter, alignment	2970Mbps	—	—	0.30	UI
$T_{JTIMING}$	Serial output jitter, timing	270 Mbps	—	—	0.20	UI
$T_{JTIMING}$	Serial output jitter, timing	1485 Mbps	—	—	1.0	UI
$T_{JTIMING}$	Serial output jitter, timing	2970 Mbps	—	—	2.0	UI

Notes:
1. Timing jitter is measured in accordance with SMPTE RP 184-1996, SMPTE RP 192-1996 and the applicable serial data transmission standard, SMPTE 259M-1997 or SMPTE 292M (proposed). A color bar test pattern is used.The value of f_{SCLK} is 270 MHz or 360 MHz for SMPTE 259M, 540 MHz for SMPTE 344M or 1485 MHz for SMPTE 292M serial data rates. See the Timing Jitter Bandpass section.
2. Jitter is defined in accordance with SMPTE RP1 184-1996 as: jitter at an equipment output in the absence of input jitter.
3. All Tx jitter is measured at the output of an industry standard cable driver; connection to the cable driver is via a 50 Ohm impedance differential signal from the Lattice SERDES device.
4. The cable driver drives: RL=75 Ohm, AC-coupled at 270, 1485, or 2970 Mbps, RREFLVL=RREFPRE=4.75 kOhm 1%.

Table 3-20. Receive

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
BR_{SDI}	Serial input data rate		270	—	2970	Mbps
CID	Stream of non-transitions (=Consecutive Identical Digits)		7(3G)/26(SMPTE Triple rates) @ 10-12 BER	—	—	Bits

Table 3-21. Reference Clock

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
F_{VCLK}	Video output clock frequency		27	—	74.25	MHz
DC_V	Duty cycle, video clock		45	50	55	%

HDMI (High-Definition Multimedia Interface) Electrical and Timing Characteristics

AC and DC Characteristics

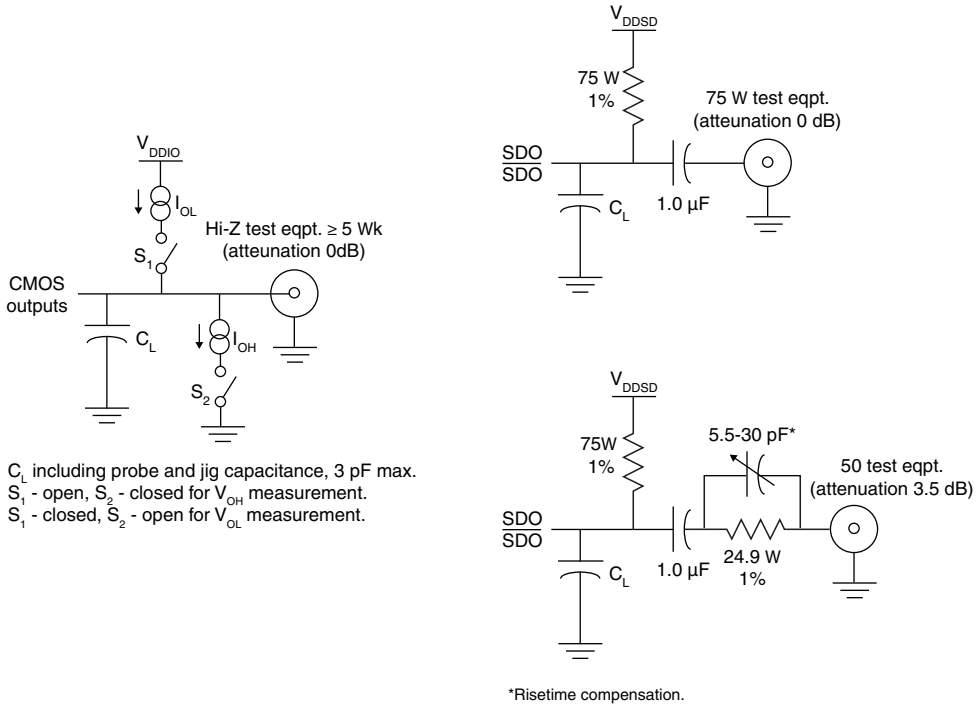
Table 3-22. Transmit and Receive[1, 2]

Symbol	Description	Spec. Compliance		Units
		Min. Spec.	Max. Spec.	
Transmit				
Intra-pair Skew		—	75	ps
Inter-pair Skew		—	800	ps
TMDS Differential Clock Jitter		—	0.25	UI
Receive				
R_T	Termination Resistance	40	60	Ohms
V_{ICM}	Input AC Common Mode Voltage (50-Ohm Setting)	—	50	mV
TMDS Clock Jitter	Clock Jitter Tolerance	—	0.25	UI

1. Output buffers must drive a translation device. Max. speed is 2 Gbps. If translation device does not modify rise/fall time, the maximum speed is 1.5 Gbps.
2. Input buffers must be AC coupled in order to support the 3.3 V common mode. Generally, HDMI inputs are terminated by an external cable equalizer before data/clock is forwarded to the LatticeECP3 device.

Figure 3-19. Test Loads

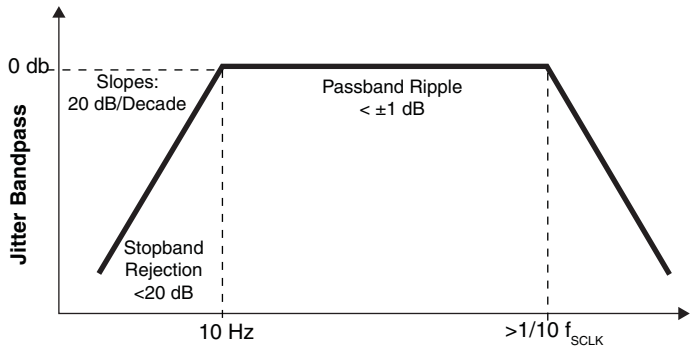
Test Loads



C_L including probe and jig capacitance, 3 pF max.
S_1 - open, S_2 - closed for V_{OH} measurement.
S_1 - closed, S_2 - open for V_{OL} measurement.

*Risetime compensation.

Timing Jitter Bandpass



PICs and DDR Data (DQ) Pins Associated with the DDR Strobe (DQS) Pin

PICs Associated with DQS Strobe	PIO Within PIC	DDR Strobe (DQS) and Data (DQ) Pins
For Left and Right Edges of the Device		
P[Edge] [n-3]	A	DQ
	B	DQ
P[Edge] [n-2]	A	DQ
	B	DQ
P[Edge] [n-1]	A	DQ
	B	DQ
P[Edge] [n]	A	[Edge]DQSn
	B	DQ
P[Edge] [n+1]	A	DQ
	B	DQ
P[Edge] [n+2]	A	DQ
	B	DQ
For Top Edge of the Device		
P[Edge] [n-3]	A	DQ
	B	DQ
P[Edge] [n-2]	A	DQ
	B	DQ
P[Edge] [n-1]	A	DQ
	B	DQ
P[Edge] [n]	A	[Edge]DQSn
	B	DQ
P[Edge] [n+1]	A	DQ
	B	DQ
P[Edge] [n+2]	A	DQ
	B	DQ

Note: “n” is a row PIC number.

Part Number	Voltage	Grade[1]	Power	Package	Pins	Temp.	LUTs (K)
LFE3-150EA-6FN672I	1.2 V	–6	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-7FN672I	1.2 V	–7	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-8FN672I	1.2 V	–8	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-6LFN672I	1.2 V	–6	LOW	Lead-Free fpBGA	672	IND	149
LFE3-150EA-7LFN672I	1.2 V	–7	LOW	Lead-Free fpBGA	672	IND	149
LFE3-150EA-8LFN672I	1.2 V	–8	LOW	Lead-Free fpBGA	672	IND	149
LFE3-150EA-6FN1156I	1.2 V	–6	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-7FN1156I	1.2 V	–7	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-8FN1156I	1.2 V	–8	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-6LFN1156I	1.2 V	–6	LOW	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-7LFN1156I	1.2 V	–7	LOW	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-8LFN1156I	1.2 V	–8	LOW	Lead-Free fpBGA	1156	IND	149

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.

Part Number	Voltage	Grade	Power	Package	Pins	Temp.	LUTs (K)
LFE3-150EA-6FN672ITW[1]	1.2 V	–6	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-7FN672ITW[1]	1.2 V	–7	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-8FN672ITW[1]	1.2 V	–8	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-6FN1156ITW[1]	1.2 V	–6	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-7FN1156ITW[1]	1.2 V	–7	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-8FN1156ITW[1]	1.2 V	–8	STD	Lead-Free fpBGA	1156	IND	149

1. Specifications for the LFE3-150EA-*sp*FN*pkg*CTW and LFE3-150EA-*sp*FN*pkg*ITW devices, (where *sp* is the speed and *pkg* is the package), are the same as the LFE3-150EA-*sp*FN*pkg*C and LFE3-150EA-*sp*FN*pkg*I devices respectively, except as specified below.
   - The CTC (Clock Tolerance Circuit) inside the SERDES hard PCS in the TW device is not functional but it can be bypassed and implemented in soft IP.
   - The SERDES XRES pin on the TW device passes CDM testing at 250V.

Date	Version	Section	Change Summary
September 2009	01.4	Architecture	Corrected link in sysMEM Memory Block section.
			Updated information for On-Chip Programmable Termination and modified corresponding figure.
			Added footnote 2 to On-Chip Programmable Termination Options for Input Modes table.
			Corrected Per Quadrant Primary Clock Selection figure.
		DC and Switching Characteristics	Modified -8 Timing data for 1024x18 True-Dual Port RAM (Read-Before-Write, EBR Output Registers)
			Added ESD Performance table.
			LatticeECP3 External Switching Characteristics table - updated data for $t_{DIBGDDR}$, t_{W_PRI}, t_{W_EDGE} and $t_{SKEW\_EDGE\_DQS}$.
			LatticeECP3 Internal Switching Characteristics table - updated data for t_{COO_PIO} and added footnote #4.
			sysCLOCK PLL Timing table - updated data for f_{OUT}.
			External Reference Clock Specification (refclkp/refclkn) table - updated data for $V_{REF\text{-}IN\text{-}SE}$ and $V_{REF\text{-}IN\text{-}DIFF}$.
			LatticeECP3 sysCONFIG Port Timing Specifications table - updated data for t_{MWC}.
			Added TRLVDS DC Specification table and diagram.
			Updated Mini LVDS table.
August 2009	01.3	DC and Switching Characteristics	Corrected truncated numbers for V_{CCIB} and V_{CCOB} in Recommended Operating Conditions table.
July 2009	01.2	Multiple	Changed references of “multi-boot” to “dual-boot” throughout the data sheet.
		Architecture	Updated On-Chip Programmable Termination bullets.
			Updated On-Chip Termination Options for Input Modes table.
			Updated On-Chip Termination figure.
		DC and Switching Characteristics	Changed min/max data for FREF_PPM and added footnote 4 in SERDES External Reference Clock Specification table.
			Updated SERDES minimum frequency.
		Pinout Information	Corrected MCLK to be I/O and CCLK to be I in Signal Descriptions table
May 2009	01.1	All	Removed references to Parallel burst mode Flash.
		Introduction	Features - Changed 250 Mbps to 230 Mbps in Embedded SERDES bulleted section and added a footnote to indicate 230 Mbps applies to 8b10b and 10b12b applications.
			Updated data for ECP3-17 in LatticeECP3 Family Selection Guide table.
			Changed embedded memory from 552 to 700 Kbits in LatticeECP3 Family Selection Guide table.
		Architecture	Updated description for CLKFB in General Purpose PLL Diagram.
			Corrected Primary Clock Sources text section.
			Corrected Secondary Clock/Control Sources text section.
			Corrected Secondary Clock Regions table.
			Corrected note below Detailed sysDSP Slice Diagram.
			Corrected Clock, Clock Enable, and Reset Resources text section.
			Corrected ECP3-17 EBR number in Embedded SRAM in the LatticeECP3 Family table.
			Added On-Chip Termination Options for Input Modes table.
			Updated Available SERDES Quads per LatticeECP3 Devices table.